

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A solid-state imaging device comprising:

a semiconductor substrate on which solid-state imaging elements are formed;

a translucent member provided onto a surface of the semiconductor substrate such that spaces are provided to be opposed to light receiving areas of the solid-state imaging devices, and

a through-hole which are formed in the semiconductor substrate, wherein

said solid-state imaging device is electrically connected to an external contact terminal by way of said through-hole,

wherein the translucent member is connected to the semiconductor substrate via spacers, and wherein the spacers are formed of same material as the translucent member.

2. (Currently Amended) A solid-state imaging device according to claim 1, wherein said external contact terminal is formed on a surface of the semiconductor substrate, said surface being opposed to another surface thereof where the solid-state imaging ~~element is~~ elements are formed.

3. (Currently Amended) A solid-state imaging device according to claim 1, said solid-state imaging device further comprising a reinforcing plate which is contacted at a surface side of the semiconductor substrate, said surface side being opposed to another surface of the semiconductor substrate where the solid-state imaging ~~element is~~ elements are formed, wherein

said external contact terminal is arranged at a surface of the reinforcing plate, said surface being opposed to another

surface of the reinforcing plate where contact between the semiconductor substrate and the reinforcing plate is made.

4. (Canceled).

5. (Canceled).

6. (Amended) A solid-state imaging device comprising:
a semiconductor substrate on which solid-state imaging
elements are formed;

a translucent member provided onto a surface of the
semiconductor substrate such that spaces are provided to be
opposed to light receiving areas of the solid-state imaging
devices, and

a through-hole which are formed in the semiconductor
substrate, wherein

said solid-state imaging device is electrically connected
to an external contact terminal by way of said through-hole,

wherein the translucent member is connected to the
semiconductor substrate via spacers, and ~~A solid-state imaging~~
~~device according to claim 4,~~ wherein the spacers are formed of
same material as the semiconductor substrate.

7. (Canceled).

8. (Currently Amended) A solid-state imaging device
comprising:

a semiconductor substrate on which solid-state imaging
elements are formed;

a translucent member provided onto a surface of the
semiconductor substrate such that spaces are provided to be
opposed to light receiving areas of the solid-state imaging

devices, and

a through-hole which are formed in the semiconductor substrate, wherein

said solid-state imaging device is electrically connected to an external contact terminal by way of said through-hole,

wherein the translucent member is connected to the semiconductor substrate via spacers, and ~~A solid-state imaging device according to claim 7,~~ wherein the spacers are formed of silicon.

9. (Currently Amended) A solid-state imaging device comprising:

a semiconductor substrate on which solid-state imaging elements are formed;

a translucent member provided onto a surface of the semiconductor substrate such that spaces are provided to be opposed to light receiving areas of the solid-state imaging devices, and

a through-hole which are formed in the semiconductor substrate, wherein

said solid-state imaging device is electrically connected to an external contact terminal by way of said through-hole,

wherein the translucent member is connected to the semiconductor substrate via spacers, and ~~A solid-state imaging device according to claim 7,~~ wherein the spacers are formed of 42 alloy.

10. (Original) A solid-state imaging device according to claim 1, wherein said through-hole is filled with a conductive material in an inner wall thereof with an insulating film being formed in-between.

11. (Original) A solid-state imaging device according to claim 10, said insulating film is made of silicon oxide.

12. (Original) A solid-state imaging device according to claim 10 or 11, thickness of said insulating film is no less than $0.5\mu\text{m}$.

13. (Withdrawn - Currently Amended) A solid-state imaging device manufacturing method, comprising the steps of:

a step of forming a semiconductor substrate on a surface of which a plurality of solid-state imaging devices are arranged and on a back surface side of which external connecting terminals are arranged such that the external connecting terminals are connected electrically to the solid-state imaging devices via through-holes;

a step of ~~jointing~~joining a translucent member to a surface of the semiconductor substrate such that spaces are provided to oppose to light receiving areas of the solid-state imaging devices; and

a step of separating a ~~jointed~~joined body obtained in ~~jointing~~joining step into individual solid-state imaging devices.

14. (Withdrawn - Currently Amended) A solid-state imaging device manufacturing method, according to claim 13, wherein the step of ~~jointing~~joining the translucent member includes the steps of,

preparing a translucent member having a plurality of concave portions at positions that correspond to solid-state imaging device forming regions, and

~~jointing~~joining the translucent member to a surface of

the semiconductor substrate.

15. (Withdrawn - Currently Amended) A solid-state imaging device manufacturing method, according to claim 13, further comprising, prior to the step of ~~jointing~~ joining, the step of forming projected portions on a surface of the semiconductor substrate to surround the light receiving areas;

wherein spaces are formed between the light receiving areas and the translucent member by the projected portions.

16. (Withdrawn - Currently Amended) A solid-state imaging device manufacturing method, according to claim 14, wherein the step of ~~jointing~~ joining is executed to form spaces between the semiconductor substrate and the translucent member via spacers that are arranged to surround the light receiving areas.

17. (Withdrawn) A solid-state imaging device manufacturing method, according to claim 13, wherein said method is further comprising the steps of:

a step of forming solid-state imaging elements on a surface of the semiconductor substrate;

a step of forming through-holes at a surface of the semiconductor substrate;

a step of forming an insulating film in inner walls of the through-holes, and

a step of filling conductive material in the through-holes.

18. (Withdrawn) A solid-state imaging device manufacturing method, according to claim 17, wherein the step of forming the insulating film includes a cold CVD method.

19. (Withdrawn) A solid-state imaging device manufacturing

method, according to claim 18, wherein the step of filling conductive material includes a vacuum screen-printing method.